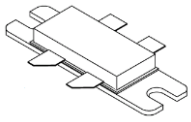
MK011K0EPX LDMOS TRANSISTOR

Document Number: MK011K0EPX
Advanced Datasheet V1.0

1000W/600W, 65V/50V High Power RF LDMOS FETs

MK011K0EPX



Description

The MK011K0EPX is a 1000W capable, highly rugged, unmatched LDMOS FET, designed for commercial and industrial applications with frequencies HF to 250MHz.

It is featured for industry leading high power and high ruggedness, suitable for Industrial, Scientific and Medical application, as well as HF communication, VHF TV and Aerospace applications.

Freq(MHz)	Voltage(V)	Signal type	Pin(dBm)	Pout(W)	Power Gain(dB)	Eff(%)	Remark
108	65	CW	41.3	1100	19.1	82	Balun
108	50	CW	40	650	18.8	82	Balun

Features

- High breakdown voltage 190V to enable possible class E operation at lower Vdd up to 50V
- Qualified up to a maximum of VDS = 65 V Class AB
- Characterized from 36 V to 65 V to support a wide range of applications
- High Efficiency and Linear Gain Operations
- On chip RC network enable high stability and ruggedness
- Integrated ESD Protection
- Large Positive and Negative Gate/Source Voltage Range for Improved Class C Operation
- Excellent thermal stability, low HCI drift
- Compliant to Restriction of Hazardous Substances (RoHS) Directive 2002/95/EC

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain—Source Voltage	V_{DSS}	190	Vdc
Gate—Source Voltage	V_{GS}	-10 to +10	Vdc
Operating Voltage	V_{DD}	+65	Vdc
Storage Temperature Range	T_{stg}	-65 to +150	°C
Case Operating Temperature	T_C	+150	°C
Operating Junction Temperature	T_J	+225	°C

Table 2. Thermal Characteristics

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case ,Case Temperature 85°C, 1700W CW, 65 Vdc, I_{DQ} = 240 mA	$R_{\theta JC}$	TBD	°C/W
Transient thermal impedance from junction to case Tj = 150° C; tp = 100 us; Duty cycle = 20 %	Zth	TBD	°C/W

Table 3. ESD Protection Characteristics

Test Methodology	Class
Human Body Model (per JESD22—A114)	Class 2

Table 4. Electrical Characteristics (TA = 25 ℃ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit

DC Characteristics

Drain-Source Voltage V_{GS}=0V, I_{DS}=20.0 mA	$V_{(BR)DSS}$		190		V
Zero Gate Voltage Drain Leakage Current (V_{DS} = 55V, V_{GS} = 0 V)	I_{DSS}	——	——	1	μA
Gate—Source Leakage Current (V_{GS} = 10 V, V_{DS} = 0 V)	I_{GSS}	——	——	1	μA
Gate Threshold Voltage (V_{DS} = 55V, I_D = 600 μA)	$V_{GS}(th)$	——	2.6	——	V
Gate Quiescent Voltage (V_{DD} = 60 V, I_D = 240 mA, Measured in Functional Test)	$V_{GS(Q)}$	——	3	——	V
Drain source on state resistance (V_{DS} = 0.1V, V_{GS} = 10 V) Each section side of device measured	Rds(on)		200		mΩ
Common Source Input Capacitance (V_{GS} = 0V, V_{DS} =65 V, f = 1 MHz) Each section side of device measured	C_{ISS}		560		pF
Common Source Output Capacitance (V_{GS} = 0V, V_{DS} =65 V, f = 1 MHz) Each section side of device measured	C_{OSS}		90		pF
Common Source Feedback Capacitance (V_{GS} = 0V, V_{DS} =65 V, f = 1 MHz) Each section side of device measured	C_{RSS}		2		pF

108MHz

Reference Circuit of Test Fixture (108MHz Power Amplifier)

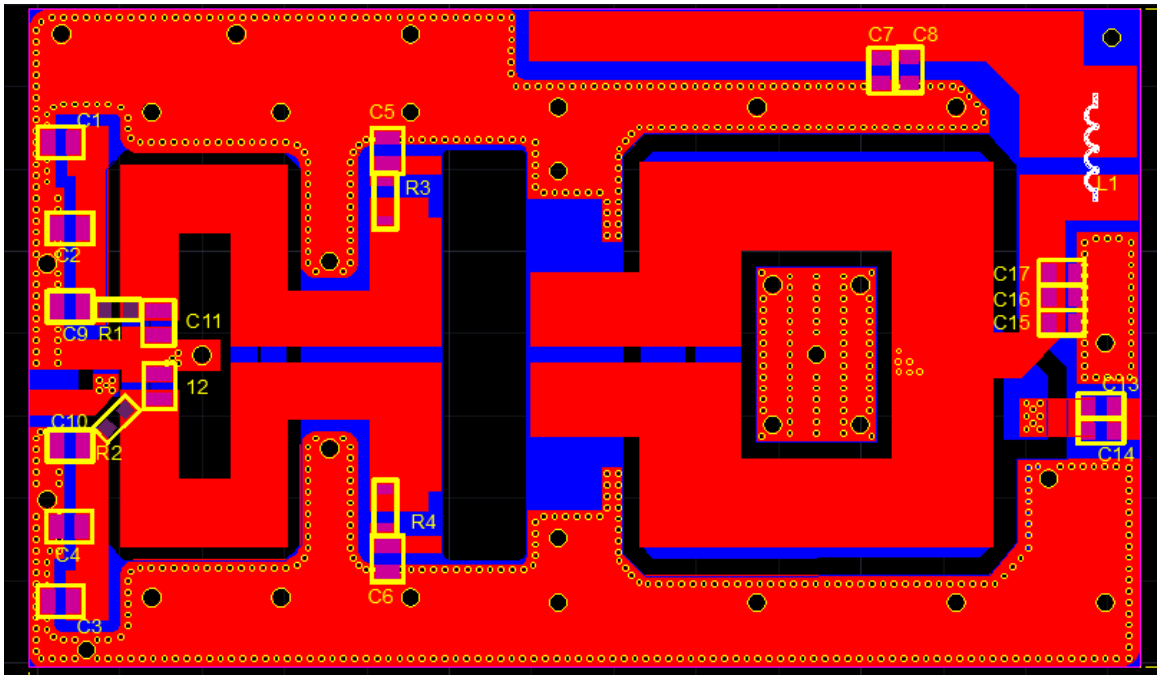
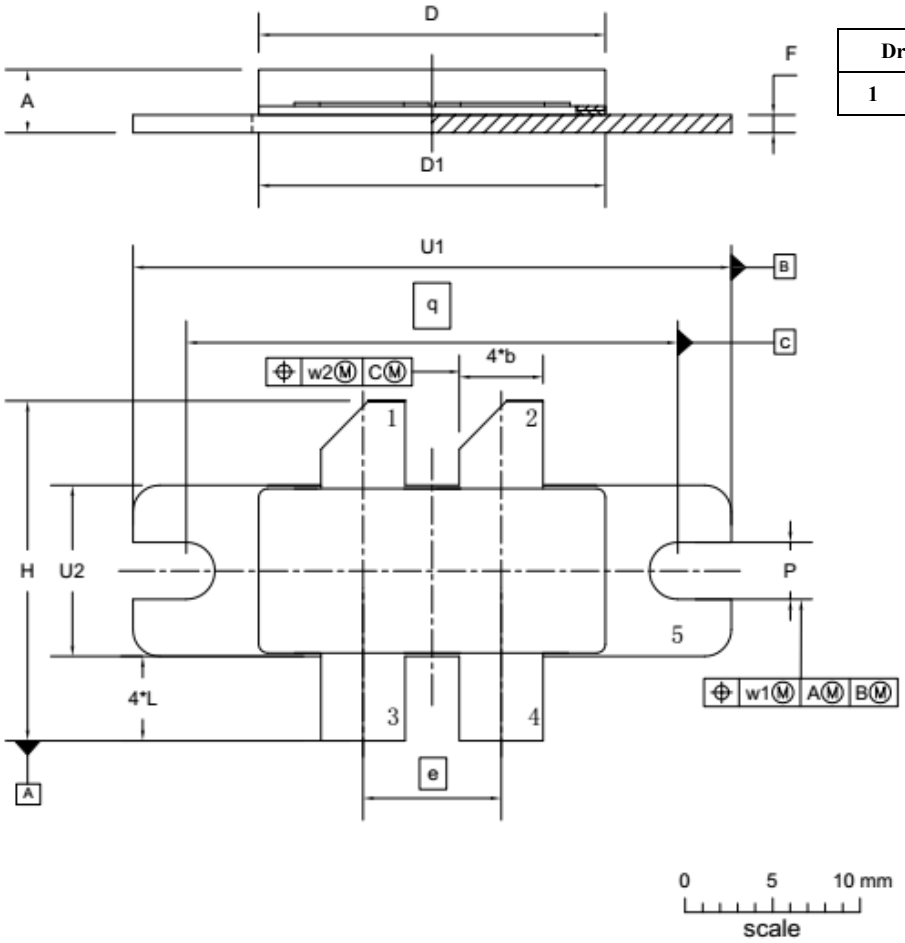


Table 5. Test Circuit Component Designations and Values

Component	Description	Suggestion
C1~C4,C7,C8	10uF/200V-1210	Ceramic multilayer capacitor
C9~C12	560pF	
C5,C6	1000pF	
C13~C17	470pF	
R1,R2	240 Ω /1206	Chip Resistor
R3,R4	25 Ω 2512	Chip Resistor
L1	1.5mm wire， 5mm innerdiameter，7turns	DIY

Package Outline

Eared Flanged Ceramic Package; 2 mounting holes; 4 leads



Drain		Gate		Source
1	2	3	4	5

UNIT	A	b	c	D	D_1	e	E	F	H	L	p	Q	q	U_1	U_2	W_1	W_2
mm	4.72 3.43	4.93 4.67	0.15 0.08	20.02 19.61	19.96 19.66	7.90	9.50 9.30	1.14 0.89	19.94 18.92	5.33 4.32	3.38 3.12	1.70 1.45	27.94	34.16 33.91	9.91 9.65	0.25	0.51
inches	0.186 0.135	0.194 0.184	0.006 0.003	0.788 0.772	0.786 0.774	0.311	0.374 0.366	0.045 0.035	0.785 0.745	0.210 0.170	0.133 0.123	0.067 0.057	1.100	1.345 1.335	0.390 0.380	0.01	0.02

OUTLINE VERSION	REFERENCE			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
PKG-B4E					03/12/2013

Revision history

Table 5. Document revision history

Date	Revision	Datasheet Status
2026/3/6	Rev 1.0	Advanced Datasheet

Application data based on TC-26-06

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